Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Freescale Semiconductor
Data Sheet: Technical Data

Document Number: MPC8548E
Rev. 9, 02/2012

MPC8548E PowerQUICC III Integrated Processor Hardware Specifications

1 Overview

This section provides a high-level overview of the device features. The following figure shows the major functional units within the device.

Although this document is written from the perspective of the MPC8548E, most of the material applies to the other family members, such as MPC8547E, MPC8545E, and MPC8543E. When specific differences occur, such as pinout differences and processor frequency ranges, they are identified as such.

For specific PVR and SVR numbers, see the *MPC8548E PowerQUICC III Integrated Host Processor Reference Manual.*

Contents

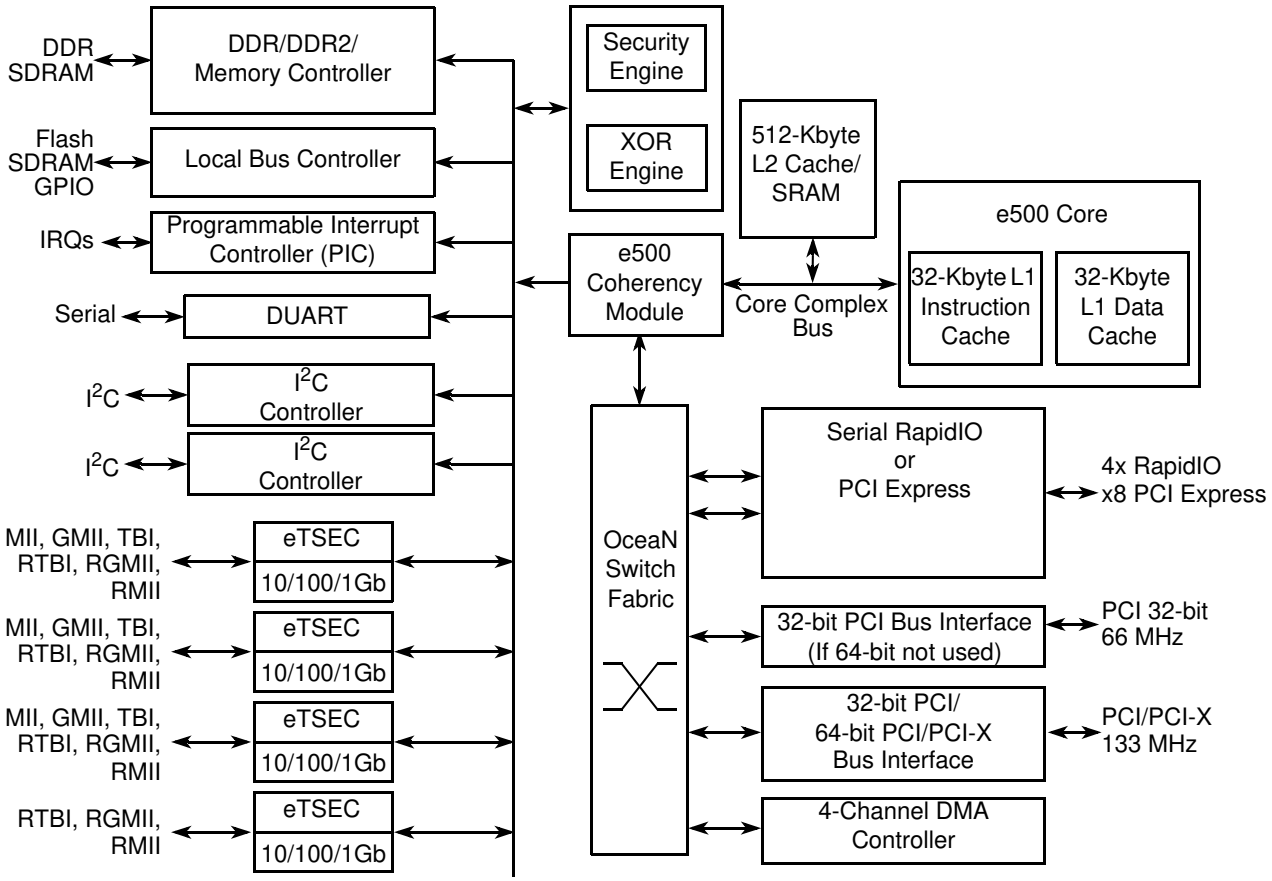


Figure 1. Device Block Diagram

1.1 Key Features

The following list provides an overview of the device feature set:

- High-performance 32-bit core built on Power Architecture® technology.
  - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection. Caches can be locked entirely or on a per-line basis, with separate locking for instructions and data.
  - Signal-processing engine (SPE) APU (auxiliary processing unit). Provides an extensive instruction set for vector (64-bit) integer and fractional operations. These instructions use both the upper and lower words of the 64-bit GPRs as they are defined by the SPE APU.
  - Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
  - 36-bit real addressing
  - Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
  - Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte to 4-Gbyte page sizes.
  - Enhanced hardware and software debug support

— Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 512-Kbyte L2 cache/SRAM
  - — Flexible configuration.
  - — Full ECC support on 64-bit boundary in both cache and SRAM modes
  - — Cache mode supports instruction caching, data caching, or both.
  - — External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
  - — 1, 2, or 4 ways can be configured for stashing only.
  - — Eight-way set-associative cache organization (32-byte cache lines)
  - — Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - — Global locking and Flash clearing done through writes to L2 configuration registers
  - — Instruction and data locks can be Flash cleared separately.
  - — SRAM features include the following:
    - – I/O devices access SRAM regions by marking transactions as snoopable (global).
    - – Regions can reside at any aligned location in the memory map.
    - – Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - — Eight local access windows define mapping within local 36-bit address space.
  - — Inbound and outbound ATMUs map to larger external address spaces.
    - – Three inbound windows plus a configuration window on PCI/PCI-X and PCI Express
    - – Four inbound windows plus a default window on RapidIO™
    - – Four outbound windows plus default translation for PCI/PCI-X and PCI Express
    - – Eight outbound windows plus default translation for RapidIO with segmentation and sub-segmentation support
- DDR/DDR2 memory controller
  - — Programmable timing supporting DDR and DDR2 SDRAM
  - — 64-bit data interface
  - — Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
  - — DRAM chip configurations from 64 Mbits to 4 Gbits with ×8/×16 data ports
  - — Full ECC support
  - — Page mode support
    - – Up to 16 simultaneous open pages for DDR

  - Up to 32 simultaneous open pages for DDR2
- Contiguous or discontiguous memory mapping
- Read-modify-write support for RapidIO atomic increment, decrement, set, and clear transactions
- Sleep mode support for self-refresh SDRAM
- On-die termination support when using DDR2
- Supports auto refreshing
- On-the-fly power management using CKE signal
- Registered DIMM support
- Fast memory access via JTAG port
- 2.5-V SSTL_2 compatible I/O (1.8-V SSTL_1.8 for DDR2)
- Support for battery-backed main memory

- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture.
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high-resolution timers/counters that can generate interrupts
  - Supports a variety of other internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing.
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
  - Interrupt summary registers allow fast identification of interrupt source.
- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, WTLS/WAP, SSL/TLS, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 2048 bits
    - Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 511 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES

  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)

  - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8, 16, or 32 bits)
- Four enhanced three-speed Ethernet controllers (eTSECs)
  - Three-speed support (10/100/1000 Mbps)
  - Four controllers designed to comply with IEEE Std. 802.3®, 802.3u, 802.3x, 802.3z, 802.3ac, and 802.3ab
  - Support for various Ethernet physical interfaces:
    - 1000 Mbps full-duplex IEEE 802.3 GMII, IEEE 802.3z TBI, RTBI, and RGMII
    - 10/100 Mbps full and half-duplex IEEE 802.3 MII, IEEE 802.3 RGMII, and RMII
  - Flexible configuration for multiple PHY interface configurations. See Section 8.1, "Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics," for more information.
  - TCP/IP acceleration and QoS features available
    - IP v4 and IP v6 header recognition on receive
    - IP v4 header checksum verification and generation
    - TCP and UDP checksum verification and generation
    - Per-packet configurable acceleration
    - Recognition of VLAN, stacked (queue in queue) VLAN, IEEE Std 802.2™, PPPoE session, MPLS stacks, and ESP/AH IP-security headers
    - Supported in all FIFO modes
  - Quality of service support:
    - Transmission from up to eight physical queues
    - Reception to up to eight physical queues
  - Full- and half-duplex Ethernet support (1000 Mbps supports only full duplex):
    - IEEE 802.3 full-duplex flow control (automatic PAUSE frame generation or software-programmed PAUSE frame generation and recognition)
  - Programmable maximum frame length supports jumbo frames (up to 9.6 Kbytes) and IEEE Std. 802.1™ virtual local area network (VLAN) tags and priority
  - VLAN insertion and deletion
    - Per-frame VLAN control word or default VLAN for each eTSEC
    - Extracted VLAN control word passed to software separately
  - Retransmission following a collision
  - CRC generation and verification of inbound/outbound frames
  - Programmable Ethernet preamble insertion and extraction of up to 7 bytes
  - MAC address recognition:
    - Exact match on primary and virtual 48-bit unicast addresses

  - VRRP and HSRP support for seamless router fail-over
  - Up to 16 exact-match MAC addresses supported
  - Broadcast address (accept/reject)
  - Hash table match on up to 512 multicast addresses
  - Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache

- OCeaN switch fabric
  - Full crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
  - PCI 2.2 and PCI-X 1.0 compatible
  - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
  - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
  - Host and agent mode support
  - 64-bit dual address cycle (DAC) support
  - PCI-X supports multiple split transactions
  - Supports PCI-to-memory and memory-to-PCI streaming

  - Memory prefetching of PCI read accesses
  - Supports posting of processor-to-PCI and PCI-to-memory writes
  - PCI 3.3-V compatible
  - Selectable hardware-enforced coherency
- Serial RapidIO™ interface unit
  - Supports *RapidIO™ Interconnect Specification, Revision 1.2*
  - Both 1× and 4× LP-serial link interfaces
  - Long- and short-haul electricals with selectable pre-compensation
  - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
  - Auto detection of 1- and 4-mode operation during port initialization
  - Link initialization and synchronization
  - Large and small size transport information field support selectable at initialization time
  - 34-bit addressing
  - Up to 256 bytes data payload
  - All transaction flows and priorities
  - Atomic set/clr/inc/dec for read-modify-write operations
  - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
  - Receiver-controlled flow control
  - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
  - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
  - Hardware recovery only
  - Register support is not required for software-mediated error recovery.
  - Accept-all mode of operation for fail-over support
  - Support for RapidIO error injection
  - Internal LP-serial and application interface-level loopback modes
  - Memory and PHY BIST for at-speed production test
- RapidIO-compatible message unit
  - 4 Kbytes of payload per message
  - Up to sixteen 256-byte segments per message
  - Two inbound data message structures within the inbox
  - Capable of receiving three letters at any mailbox
  - Two outbound data message structures within the outbox
  - Capable of sending three letters simultaneously
  - Single segment multicast to up to 32 devIDs
  - Chaining and direct modes in the outbox

  - Single inbound doorbell message structure
  - Facility to accept port-write messages
- PCI Express interface
  - PCI Express 1.0a compatible
  - Supports x8,x4,x2, and x1 link widths
  - Auto-detection of number of connected lanes
  - Selectable operation as root complex or endpoint
  - Both 32- and 64-bit addressing
  - 256-byte maximum payload size
  - Virtual channel 0 only
  - Traffic class 0 only
  - Full 64-bit decode with 32-bit wide windows
- Pin multiplexing for the high-speed I/O interfaces supports one of the following configurations:
  - 8 PCI Express
  - 4 PCI Express and 4 serial RapidIO
- Power management
  - Supports power saving modes: doze, nap, and sleep
  - Employs dynamic power management, which automatically minimizes power consumption of blocks when they are idle
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the eight counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- JTAG boundary scan, designed to comply with IEEE Std. 1149.1™

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the device. This device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.21	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.21	V	—
Core power supply for SerDes transceivers		SV_{DD}	–0.3 to 1.21	V	—
Pad power supply for SerDes transceivers		XV_{DD}	–0.3 to 1.21	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	2
Three-speed Ethernet I/O voltage		LV_{DD} (for eTSEC1 and eTSEC2) TV_{DD} (for eTSEC3 and eTSEC4)	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 3.63 –0.3 to 2.75	V	3
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	4
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD}/2 + 0.3)	V	—
	Three-speed Ethernet I/O signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	4
	Local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	—	—
	DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4
	PCI/PCI-X	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

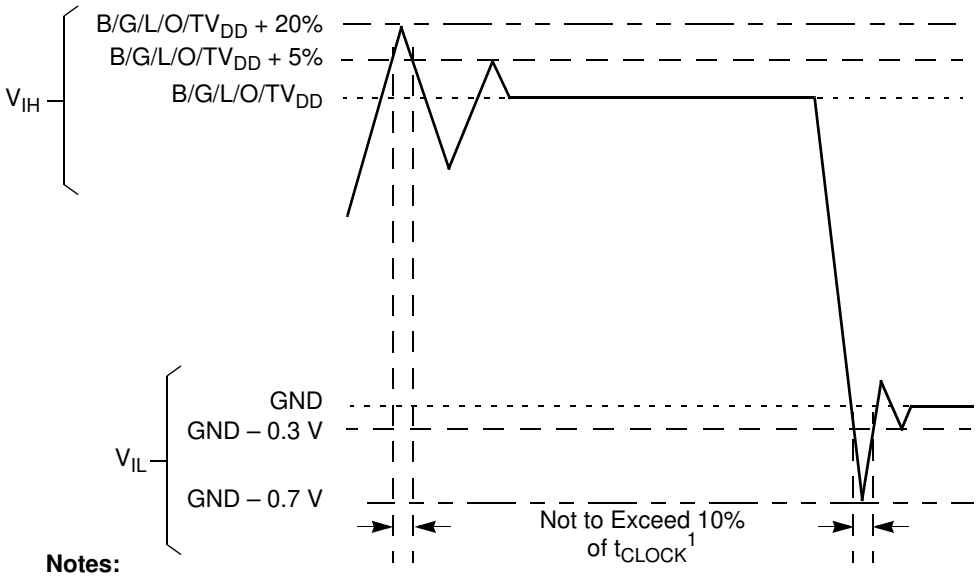
Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage		AV_{DD}	1.1 V ± 55 mV	V	1
Core power supply for SerDes transceivers		SV_{DD}	1.1 V ± 55 mV	V	—
Pad power supply for SerDes transceivers		XV_{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	—	4
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	3
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
Input voltage	DDR and DDR2 DRAM signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR and DDR2 DRAM reference	MV_{REF}	GND to $GV_{DD}/2$	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3

Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	Tj	0 to 105	°C	—

Notes:
1. This voltage is the input to the filter discussed in Section 22.2, "PLL Power Supply Filtering," and not necessarily the voltage at the AV_{DD} pin, which may be reduced from V_{DD} by the filter.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** L/TV_{IN} must not exceed L/TV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

The following figure shows the undershoot and overshoot voltages at the interfaces of this device.



Notes:
1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I^2C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For LBIU, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI*n*_CLK or SYSCLK.
   For SerDes, t_{CLOCK} references SD_REF_CLK.
2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}/BV_{DD}/TV_{DD}$

The core voltage must always be provided at nominal 1.1 V. Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR SDRAM interface uses a single-ended differential receiver referenced the externally supplied MV_{REF} signal (nominally set to $GV_{DD}/2$) as is appropriate for the SSTL2 electrical signaling standard.

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default)	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV_{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV_{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	45	OV_{DD} = 3.3 V	—
I2C	150	OV_{DD} = 3.3 V	—

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD}, AV_{DD}_n, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

4 Input Clocks

This section discusses the timing for the input clocks.

4.1 System Clock Timing

The following table provides the system clock (SYSCLK) AC timing specifications for the device.

Table 5. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV_{DD} = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	16	—	133	MHz	1, 6, 7, 8
SYSCLK cycle time	t_{SYSCLK}	7.5	—	60	ns	6, 7, 8
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies.See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The SYSCLK driver’s closed loop jitter bandwidth must be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
6. This parameter has been adjusted slower according to the workaround for device erratum GEN 13.
7. For spread spectrum clocking. Guidelines are + 0% to –1% down spread at modulation rate between 20 and 60 kHz on SYSCLK.
8. System with operating core frequency less than 1200 MHz must limit SYSCLK frequency to 100 MHz maximum.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal must be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

4.3 eTSEC Gigabit Reference Clock Timing

The following table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the device.

Table 6. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	
EC_GTX_CLK125 rise and fall time L/TVDD = 2.5 V L/TVDD = 3.3 V	t_{G125R}, t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2, 3

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV_{DD} = 2.5 V, and from 0.6 and 2.7 V for L/TV_{DD} = 3.3 V.
2. Timing is guaranteed by design and characterization.
3. EC_GTX_CLK125 is used to generate the GTX clock TSEC*n*_GTX_CLK for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the TSEC*n*_ GTX_CLK. See Section 8.2.6, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 PCI/PCI-X Reference Clock Timing

When the PCI/PCI-X controller is configured for asynchronous operation, the reference clock for the PCI/PCI-x controller is not the SYSCLK input, but instead the PCI*n*_CLK. The following table provides the PCI/PCI-X reference clock AC timing specifications for the device.

Table 7. PCI*n*_CLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV_{DD} = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
PCI*n*_CLK frequency	f_{PCICLK}	16	—	133	MHz	—
PCI*n*_CLK cycle time	t_{PCICLK}	7.5	—	60	ns	—
PCI*n*_CLK rise and fall time	t_{PCIKH}, t_{PCIKL}	0.6	1.0	2.1	ns	1, 2
PCI*n*_CLK duty cycle	$t_{PCIKHKL}/t_{PCICLK}$	40	—	60	%	2

Notes:

1. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
2. Timing is guaranteed by design and characterization.

4.5 Platform to FIFO Restrictions

Note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency ≤ platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency ≤ platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 167 MHz.

4.6 Platform Frequency Requirements for PCI-Express and Serial RapidIO

The CCB clock frequency must be considered for proper operation of the high-speed PCI-Express and Serial RapidIO interfaces as described below.

For proper PCI Express operation, the CCB clock frequency must be greater than:

$$\frac{527\ \text{MHz} \times (\text{PCI-Express link width})}{8}$$

See *MPC8548ERM, Rev. 2*, *PowerQUICC III Integrated Processor Family Reference Manual,* Section 18.1.3.2, “Link Width,” for PCI Express interface width details.

For proper serial RapidIO operation, the CCB clock frequency must be greater than:

$$\frac{2 \times (0.80) \times (\text{Serial RapidIO interface frequency}) \times (\text{Serial RapidIO link width})}{64}$$

See *MPC8548ERM, Rev. 2*, *PowerQUICC III Integrated Processor Family Reference Manual,* Section 17.4, “1x/4x LP-Serial Signal Descriptions,” for serial RapidIO interface width and frequency details.

4.7 Other Input Clocks

For information on the input clocks of other functional blocks of the platform see the specific section of this document.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	μs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	μs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	μs
Local bus PLL lock time	—	50	μs
PCI/PCI-X bus PLL lock time	—	50	μs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, "PLL Power Supply Filtering," the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that GV_{DD}(typ) = 2.5 V for DDR SDRAM, and GV_{DD}(typ) = 1.8 V for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

This table provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.15	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.15	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface. The DDR controller supports both DDR1 and DDR2 memories. DDR1 is supported with the following AC timings at data rates of 333 MHz. DDR2 is supported with the following AC timings at data rates down to 333 MHz.

6.2.1 DDR SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 1.8$ V.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V

Table 17 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 2.5$ V.

Table 17. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V

This table provides the input AC timing specifications for the DDR SDRAM interface.

Table 18. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC 533 MHz 400 MHz 333 MHz	t_{CISKEW}	 –300 –365 –390	 300 365 390	ps	1, 2

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This must be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm (T/4 - abs(t_{CISKEW}))$ where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW}.

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAS}	 1.48 1.95 2.40	 — — —	ns	3
ADDR/CMD output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAX}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCS}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCX}	 1.48 1.95 2.40	 — — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDS}, t_{DDKLDS}	 538 700 900	 — — —	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDX}, t_{DDKLDX}	 538 700 900	 — — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[*n*] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This is typically set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8548E PowerQUICC III Integrated Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe must be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[*n*] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 3 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

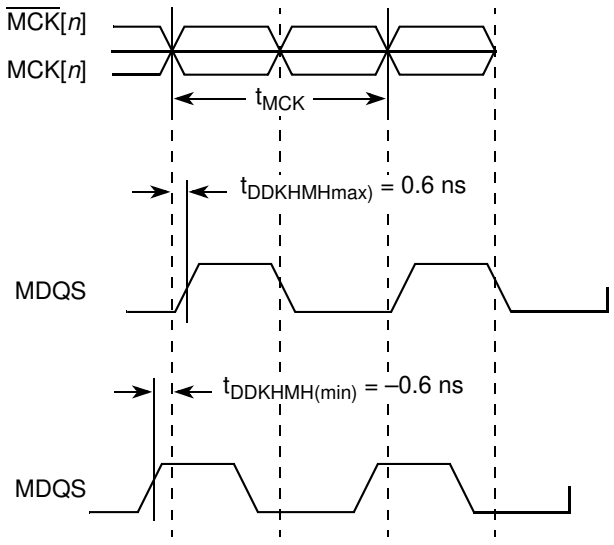


Figure 3. Timing Diagram for tDDKHMH

Figure 4 shows the DDR SDRAM output timing diagram.+

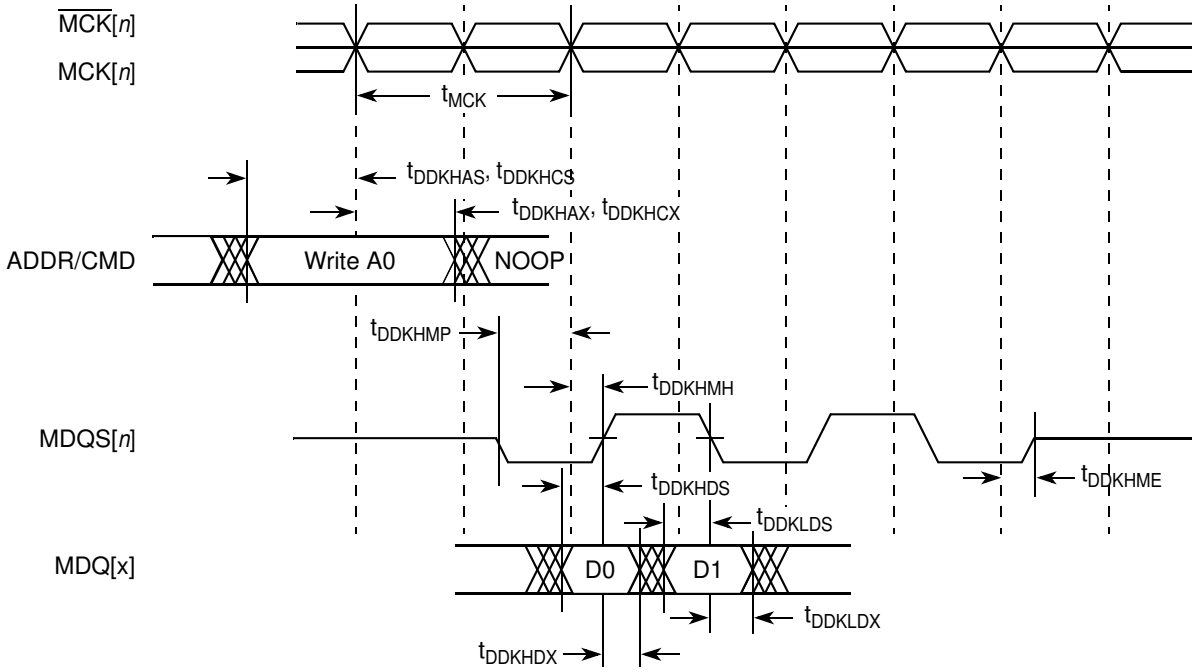


Figure 4. DDR SDRAM Output Timing Diagram

Figure 5 provides the AC test load for the DDR bus.

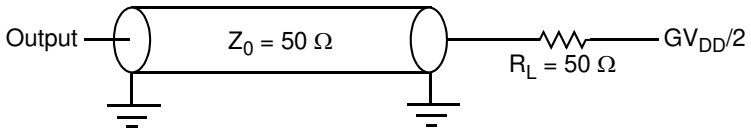


Figure 5. DDR AC Test Load